Ordering number : ENA0151B

CPH3350

P-Channel Power MOSFET
−20V, −3A, 83mΩ, Single CPH3

ON Semiconductor®
http://onsemi.com

Features

- Ultrahigh-speed switching
- 1.8V drive
- Halogen free compliance
- Protection diode in

Specifications

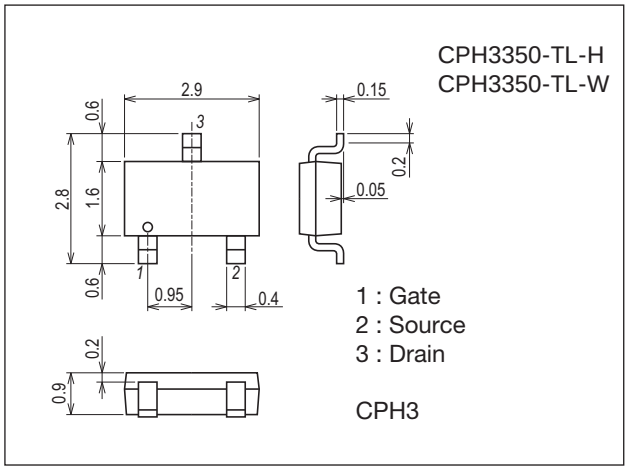
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		−20	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		−3	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−12	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

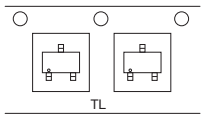
unit : mm (typ)
7015A-004



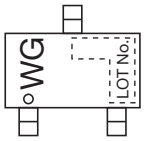
Product & Package Information

- Package : CPH3
- JEITA, JEDEC : SC-59, TO-236, SOT-23
- Minimum Packing Quantity : 3,000 pcs./reel

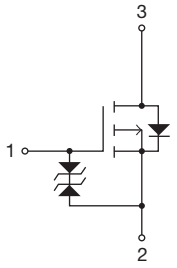
Packing Type: TL



Marking



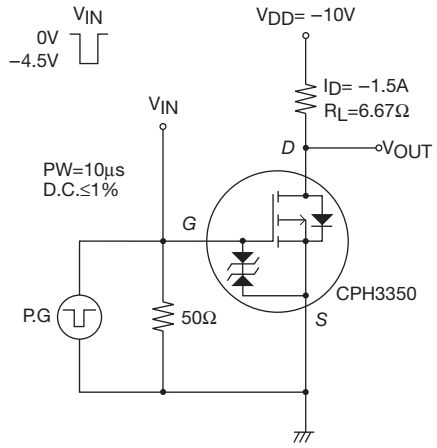
Electrical Connection



Electrical Characteristics at Ta=25°C

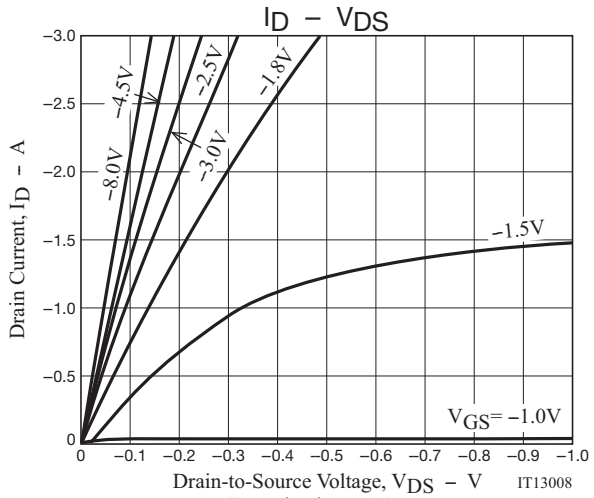
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−20V, V_{GS}=0V			−1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=−10V, I_D=−1mA	−0.4		−1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=−10V, I_D=−1.5A		4.3		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=−1.5A, V_{GS}=−4.5V		64	83	mΩ
	R_{DS}(on)2	I_D=−1A, V_{GS}=−2.5V		89	124	mΩ
	R_{DS}(on)3	I_D=−0.2A, V_{GS}=−1.8V		131	196	mΩ
Input Capacitance	Ciss	V_{DS}=−10V, f=1MHz		375		pF
Output Capacitance	Coss			77		pF
Reverse Transfer Capacitance	Crss			58		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		8.1		ns
Rise Time	t_r			26		ns
Turn-OFF Delay Time	t_{d}(off)			42		ns
Fall Time	t_f			37		ns
Total Gate Charge	Qg	V_{DS}=−10V, V_{GS}=−4.5V, I_D=−3A		4.6		nC
Gate-to-Source Charge	Qgs			0.8		nC
Gate-to-Drain “Miller” Charge	Qgd			1.3		nC
Diode Forward Voltage	V_{SD}	I_S=−3A, V_{GS}=0V		−0.83	−1.2	V

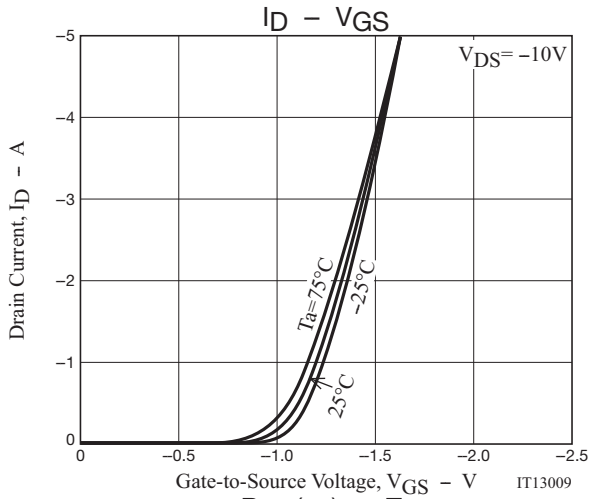
Switching Time Test Circuit

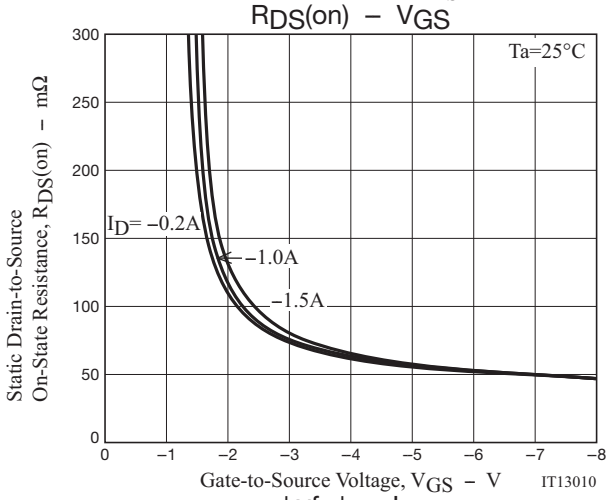


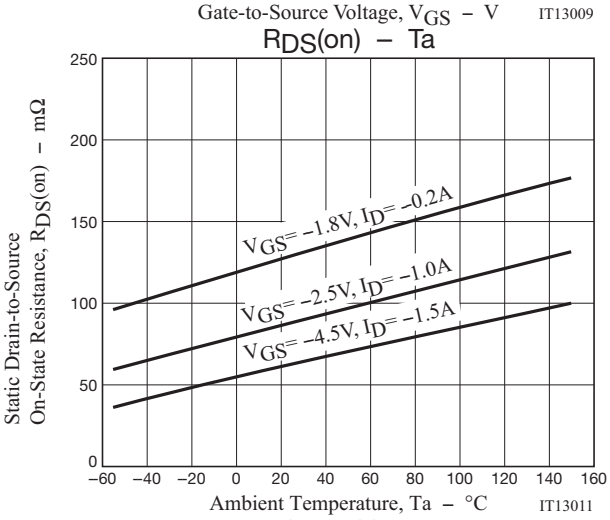
Ordering Information

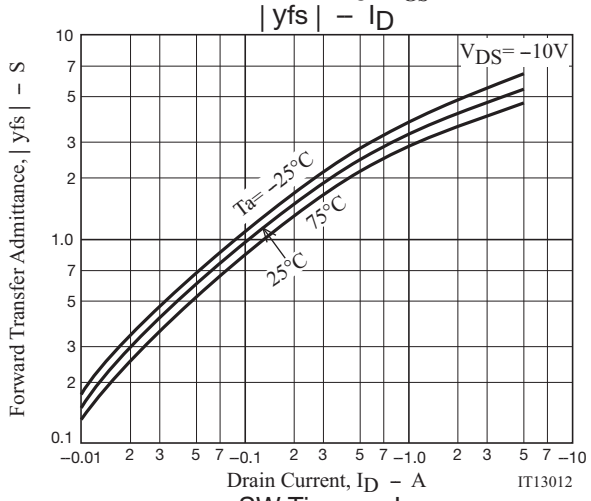
Device	Package	Shipping	memo
CPH3350-TL-H	CPH3	3,000pcs./reel	Pb Free and Halogen Free
CPH3350-TL-W			

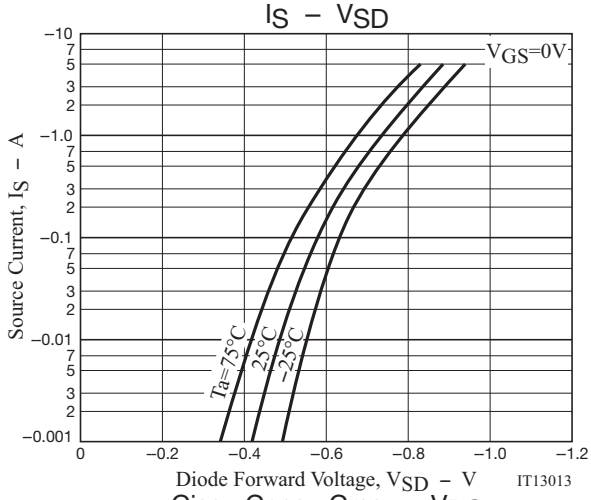

ID – VDS
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT13008
–8.0V
–4.5V
–3.0V
–2.5V
–1.8V
–1.5V
VGS= –1.0V

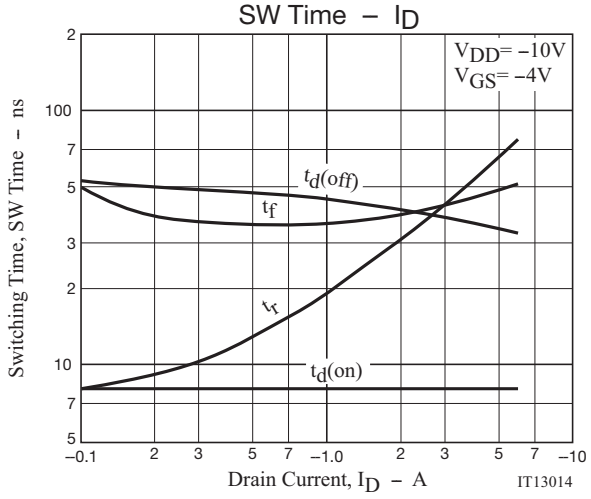

ID – VGS
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
IT13009
VDS= –10V
Ta=75°C
25°C
–25°C

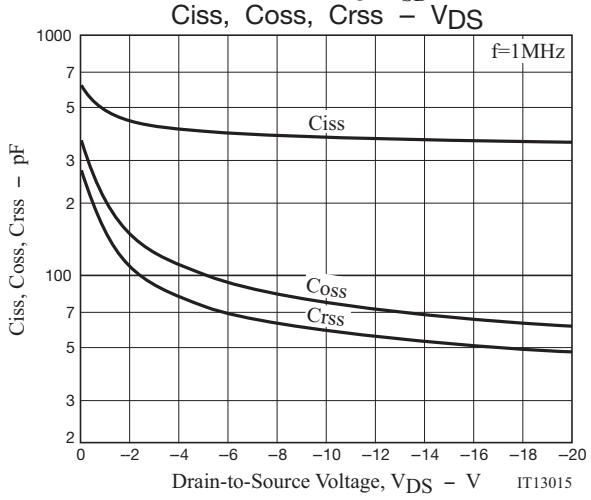

RDS(on) – VGS
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT13010
Ta=25°C
ID= –0.2A
–1.0A
–1.5A

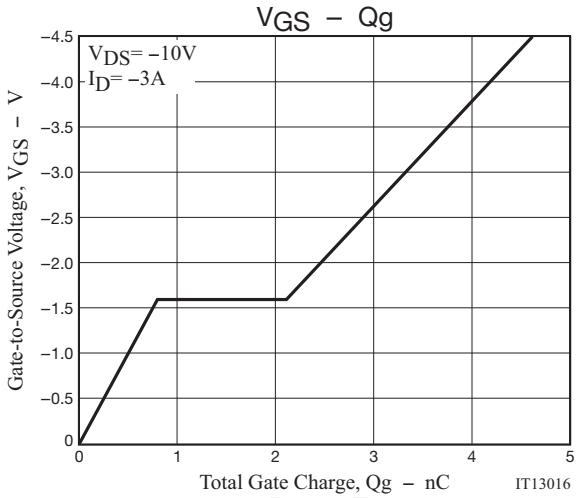

RDS(on) – Ta
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT13011
VGS= –1.8V, ID= –0.2A
VGS= –2.5V, ID= –1.0A
VGS= –4.5V, ID= –1.5A

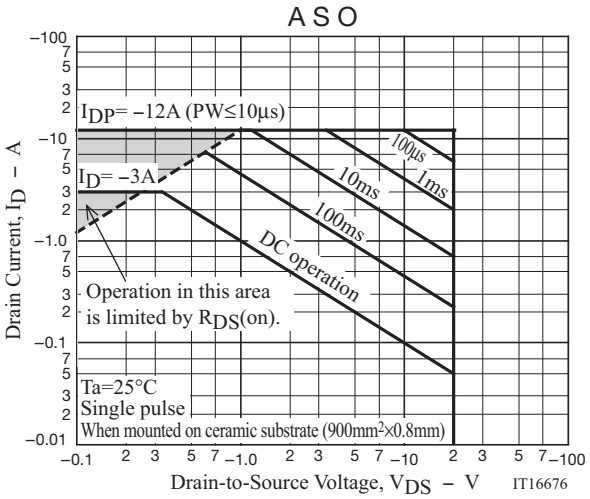

| yfs | – ID
Forward Transfer Admittance, | yfs | – S
Drain Current, ID – A
IT13012
VDS= –10V
Ta= –25°C
75°C
25°C

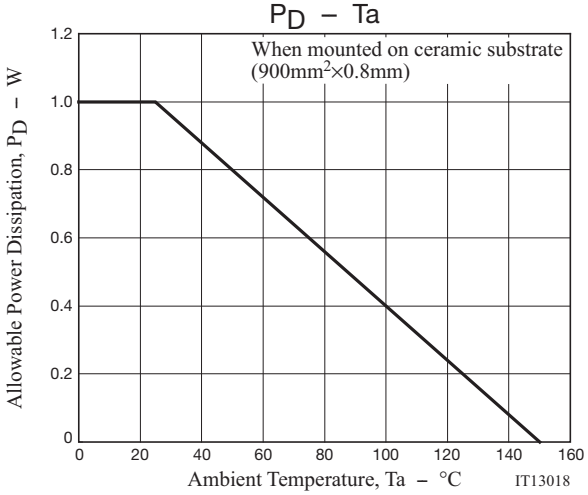

IS – VSD
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT13013
VGS=0V
Ta=75°C
25°C
–25°C


SW Time – ID
Switching Time, SW Time – ns
Drain Current, ID – A
IT13014
VDD= –10V
VGS= –4V
td(off)
tf
tr
td(on)


Ciss, Coss, Crss – VDS
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT13015
f=1MHz
Ciss
Coss
Crss

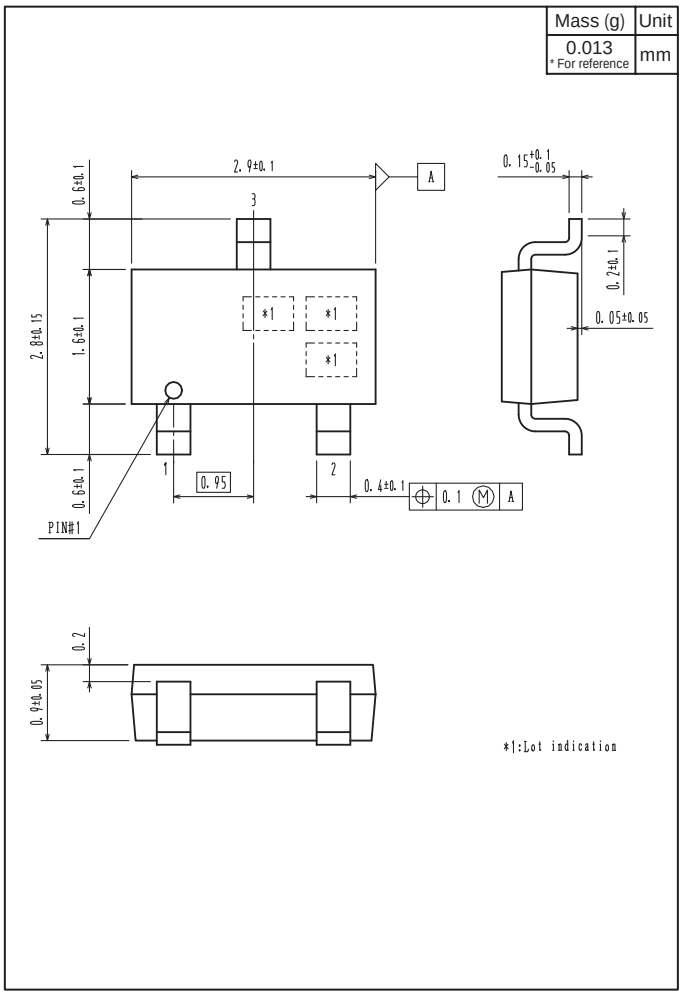

VGS – Qg
VDS= –10V
ID= –3A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT13016


A S O
IDP= –12A (PW≤10μs)
ID= –3A
100μs
1ms
10ms
100ms
DC operation
Operation in this area
is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate (900mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT16676

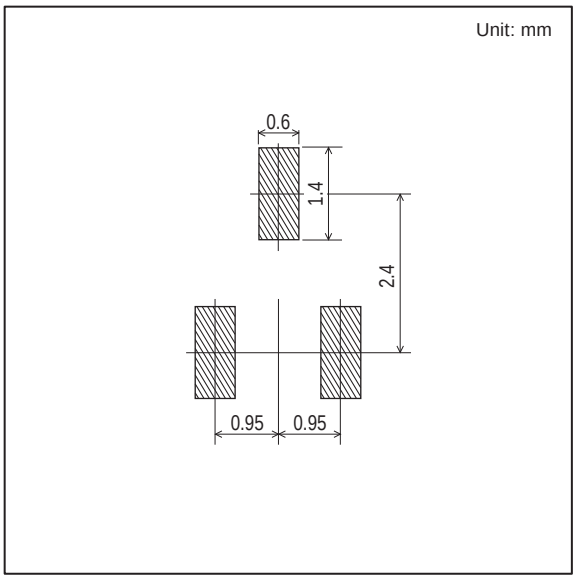

PD – Ta
When mounted on ceramic substrate
(900mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT13018

Outline Drawing

CPH3350-TL-H, CPH3350-TL-W



Land Pattern Example



Note on usage : Since the CPH3350 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.